

## **STD35NF06**

N-channel 60V - 0.018Ω - 35A - DPAK STripFET™ II Power MOSFET

#### **General features**

Туре	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD35NF06	60V	<0.020Ω	35A

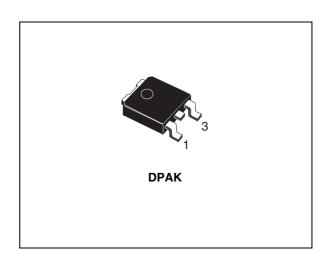
- Exceptional dv/dt capability
- Application oriented characterization
- 100% avalanche tested

### **Description**

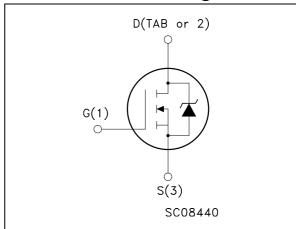
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size<sup>TM</sup>" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### **Applications**

■ Switching application



### Internal schematic diagram



#### **Order codes**

Part number	Marking	Package	Packaging	
STD35NF06T4	D35NF06T4 D35NF06		Tape & reel	

Contents STD35NF06

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STD35NF06 Electrical ratings

# 1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	60	V	
V <sub>DGR</sub>	Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)	60	V	
V <sub>GS</sub>	Gate- source voltage	± 20	V	
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25°C	35	Α	
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100°C	24.5	Α	
I <sub>DM</sub> <sup>(1)</sup>	Drain current (pulsed)	140	Α	
P <sub>tot</sub>	Total dissipation at T <sub>C</sub> = 25°C	80	W	
	Derating Factor	0.53	W/°C	
dv/dt <sup>(2)</sup>	Peak diode recovery avalanche energy 5		V/ns	
T <sub>stg</sub>	Storage temperature	55 to 175		
T <sub>j</sub>	Max. operating junction temperature	-55 to 175 °C		

<sup>1.</sup> Pulse width limited by safe operating area.

Table 2. Thermal data

Rthj-case	Thermal resistance junction-case max	1.88	°C/W
Rthj-amb	Thermal resistance junction-to ambient max	100	°C/W
T <sub>J</sub> Maximum lead temperature for soldering purpose		275	°C

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive Or Not- repetitive (pulse width limited by $T_j$ max)	17.5	А
E <sub>AS</sub>	Single pulse avalanche energy (starting $T_j = 25$ °C, $I_D = I_{AR}$ , $V_{DD} = 50$ V)	130	mJ

<sup>2.</sup>  $I_{SD}$  \$5A, di/dt \$100A/\mus,  $V_{DD} = V(BR)DSS$ ,  $T_j \le T_{JMAX}$ 

Electrical characteristics STD35NF06

# 2 Electrical characteristics

( $T_{CASE}$ =25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter Test conditions		Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	60			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS}$ = Max rating $V_{DS}$ = Max rating, $T_{C}$ = 125°C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	V
R <sub>DS(on)</sub>	Static drain-source on resistance	$V_{GS} = 10V, I_D = 17.5A$		0.018	0.020	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} > I_{D(on)} x$ $R_{DS(on)max}, I_D = 17.5A$		13		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		1300 300 105		pF pF pF
$\begin{array}{c} t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD}$ = 30V, $I_D$ = 27.5A $R_G$ = 4.7 $\Omega$ $V_{GS}$ = 10V (see <i>Figure 12</i> )		20 50 36 15		ns ns ns
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}$ = 48V, $I_D$ = 55A, $V_{GS}$ = 10V, $R_G$ = 4.7 $\Omega$ (see <i>Figure 13</i> )		44.5 10.5 17.5	60	nC nC nC

<sup>1.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5%.

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>SD</sub>	Source-drain current Source-drain current (pulsed)				35 140	A A
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	I <sub>SD</sub> = 35A, V <sub>GS</sub> = 0			1.5	V
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ = 35A, di/dt = 100A/µs, $V_{DD}$ = 20V, $T_j$ = 150°C (see <i>Figure 14</i> )		75 170 4.5		ns μC A

<sup>1.</sup> Pulse width limited by safe operating area.

<sup>2.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5%

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### 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

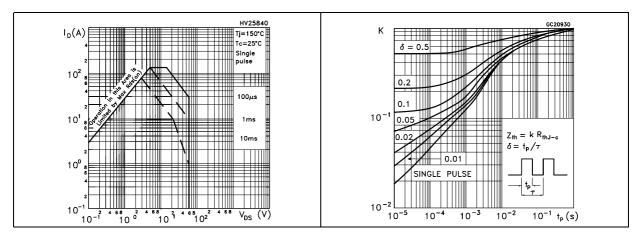


Figure 3. Output characteristics

Figure 4. Transfer characteristics

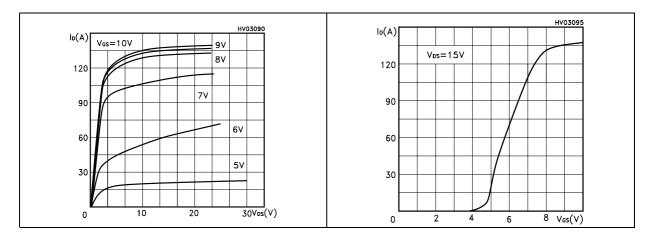
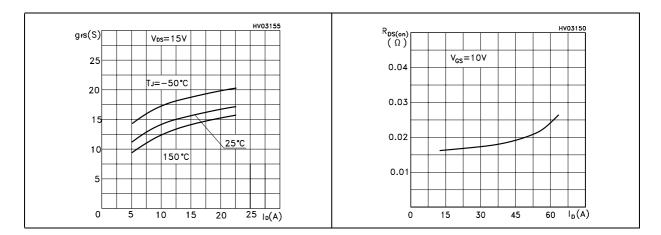


Figure 5. Transconductance

Figure 6. Static drain-source on resistance



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Figure 7. Gate charge vs. gate-source voltage Figure 8. Capacitance variations

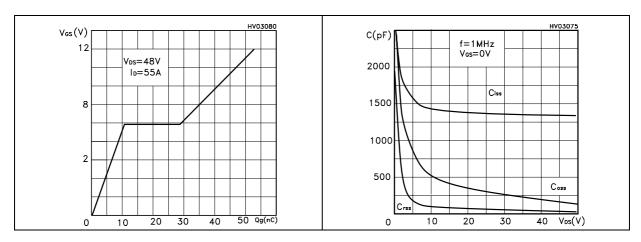


Figure 9. Normalized gate threshold voltage Figure 10. Normalized on resistance vs. vs. temperature temperature

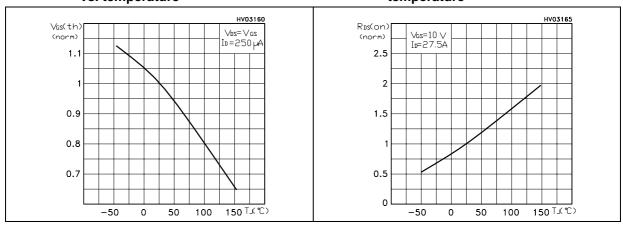
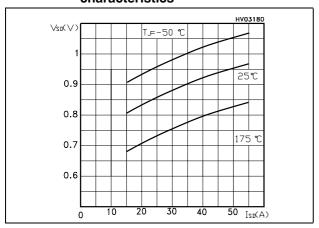


Figure 11. Source-drain diode forward characteristics



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Test circuit STD35NF06

### 3 Test circuit

Figure 12. Switching times test circuit for resistive load

Figure 13. Gate charge test circuit

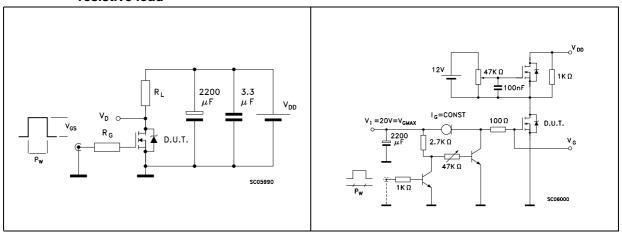


Figure 14. Test circuit for inductive load switching and diode recovery times

Figure 15. Unclamped Inductive load test circuit

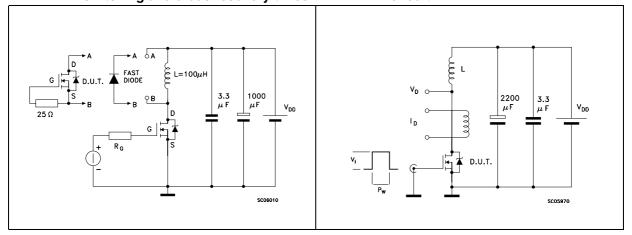
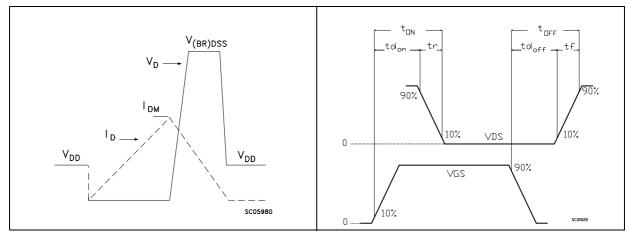


Figure 16. Unclamped inductive waveform

Figure 17. Switching time waveform

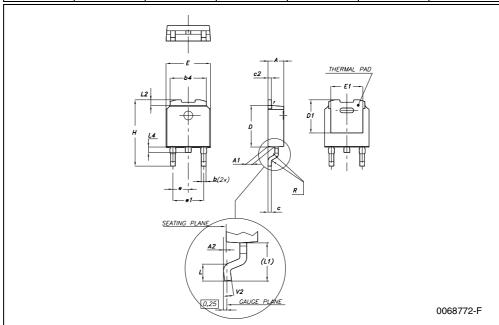


# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

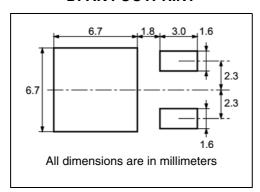
#### **DPAK MECHANICAL DATA**

D.114	mm.			inch		
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
Е	6.4		6.6	0.252		0.260
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173		0.181
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

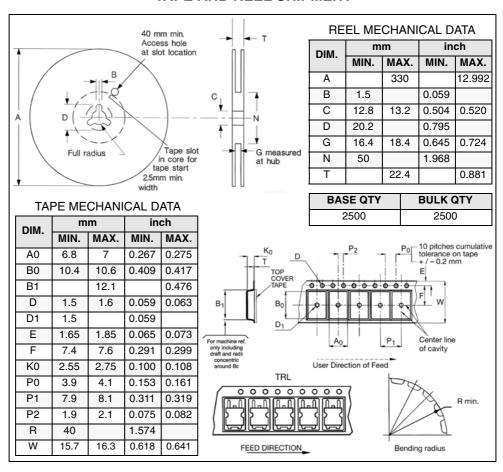


## 5 Packing mechanical data

#### **DPAK FOOTPRINT**



#### TAPE AND REEL SHIPMENT



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Revision history STD35NF06

# 6 Revision history

Table 7. Revision history

Date	Revision	Changes
21-Jun-2004	2	Preliminary version
06-Jul-2006	3	New template, no content change
20-Feb-2007	4	Typo mistake on page 1

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